

**MPS6562****PNP EPITAXIAL SILICON TRANSISTOR**

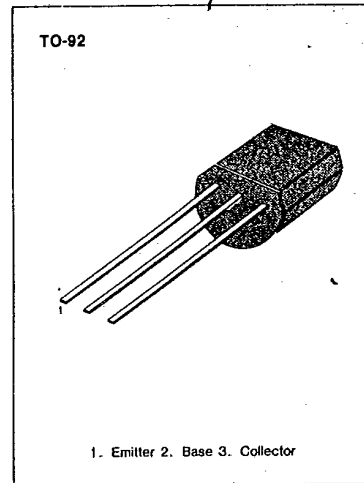
T-29-21

**AUDIO TRANSISTOR**

- Collector-Emitter Voltage:  $V_{CE0} = 25V$
- Collector Dissipation:  $P_C (\text{max}) = 625mW$
- Complement to MPS6560

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	25	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	500	mA
Collector Dissipation	$P_C$	625	mW
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 ~ 150	$^\circ C$

**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
*Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = 10mA, I_B = 0$	25			V
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = 100\mu A, I_E = 0$	25			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = 100\mu A, I_C = 0$	5			V
Collector Cut-off Current	$I_{CEO}$	$V_{CE} = 25V, I_B = 0$			100	nA
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 20V, I_E = 0$			100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 4V, I_C = 0$			100	nA
*DC Current Gain	$h_{FE}$	$I_C = 10mA, V_{CE} = 1V$	35			
		$I_C = 100mA, V_{CE} = 1V$	50			
		$I_C = 500mA, V_{CE} = 1V$	50		200	
*Collector-Emitter Saturation Voltage	$V_{CE} (\text{sat})$	$I_C = 500mA, I_B = 50mA$			0.5	V
Current Gain Bandwidth Product	$f_T$	$I_C = 10mA, V_{CE} = 10V$ $f = 30MHz$	60			MHz
*Base-Emitter On Voltage	$V_{BE} (\text{on})$	$I_C = 500mA, V_{CE} = 1V$			1.2	V
Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0$ $f = 100KHz$			30	pF

\* Pulse Test: Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$